

# Precision beam tracker for the KEK AR-TB based on SOI sensor technology

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# Introduction

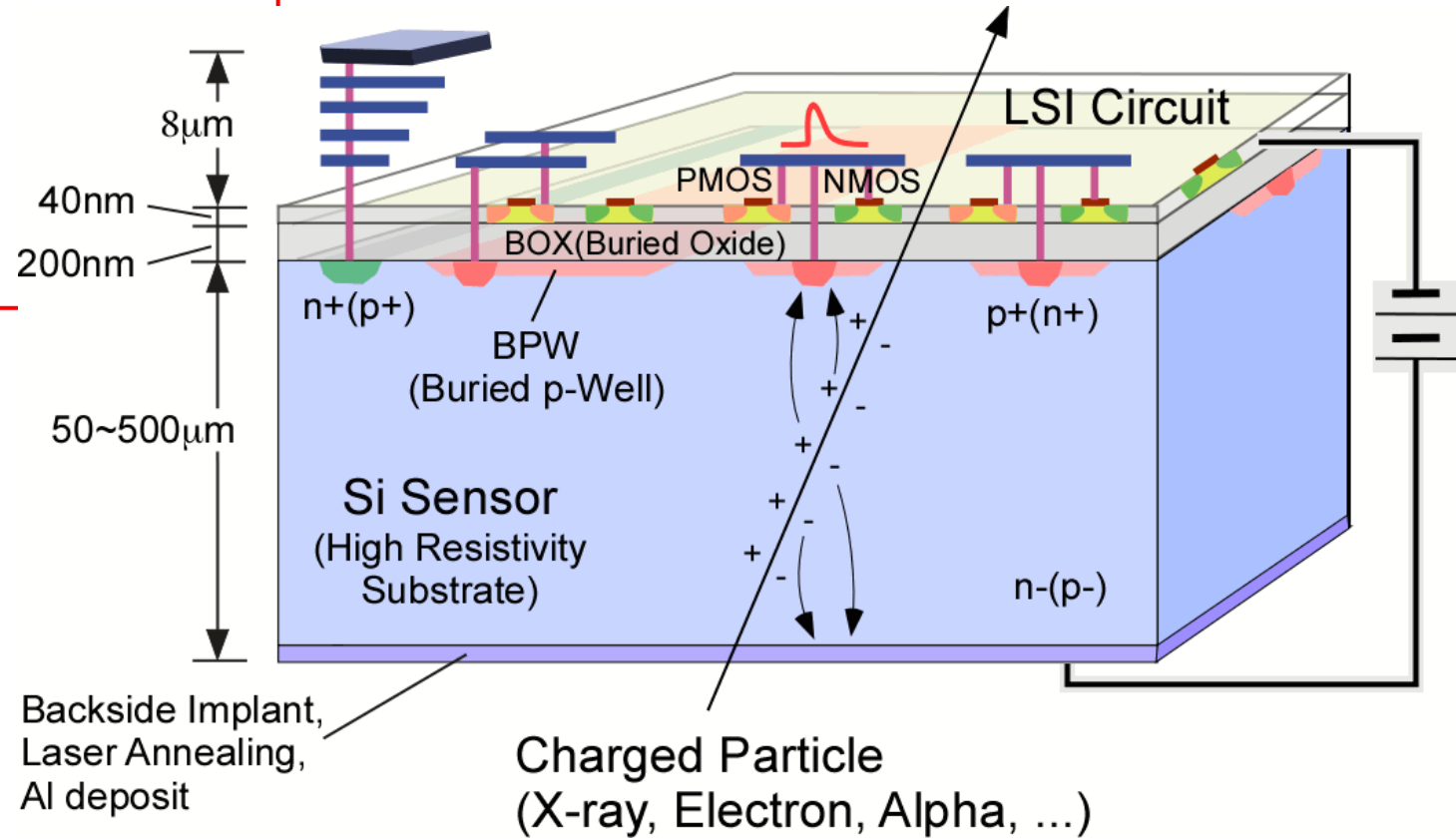
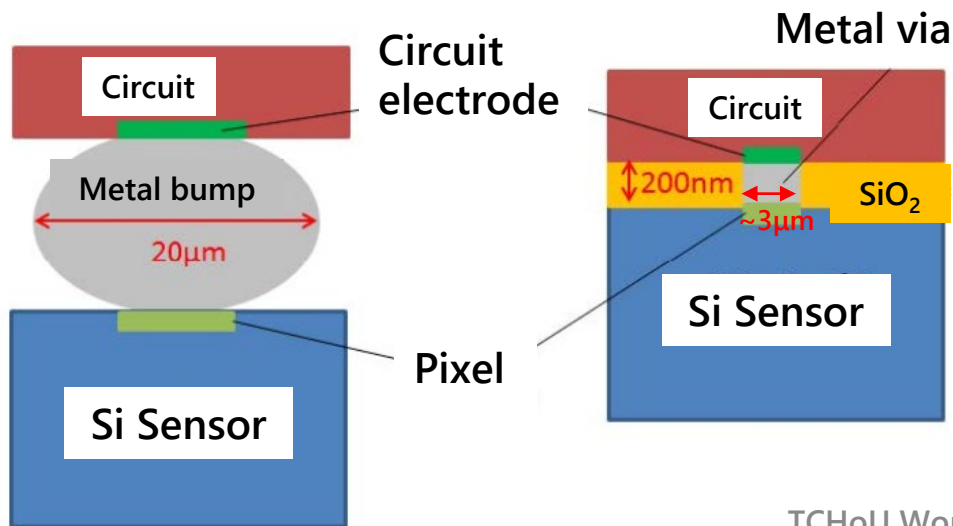
# SOI Pixel Detector

Semiconductor detector with readout circuit integrated (monolithic sensor)

Transistors are formed on buried SiO<sub>2</sub> oxide layer using **SOI** (Silicon On Insulator) technology

- SOI-CMOS  
Isolate individual transistors in oxide insulator

- Monolithic type  
→ Pixel size can be miniaturized  
sensor material can be minimized



# Motivation —KEK AR-TB & Telescope—

Necessity of GeV order test beamline for development of particle detectors in Japan

→ KEK AR-TB (Electron beamline) delivered 1st beam on March 4.

1kHz(ax at 2-3GeV), 400Hz (5GeV)

**Need a telescope with high position resolution**

**→ Telescope system with SOI pixel detectors is capable of low multiple scattering and fine intrinsic resolution**



2022/3/22

TCHoU Workshop Photon & Particle Detectors Division



# Development goals and steps

## Ultimate goal

◆ High-precision telescope system for various DUTs

## short term goal (in 2022)

◆ Evaluation of SOI Pixel Detector  
"DuTiP" (test chip for Belle 2 upgrade) in AR-Test Beamline  
→ requires Position resolution of ~10 μm

This Study

## ◆ Steps

Detector synchronization test



Oct 2021 820MeV/c e+ beam test @ELPH



GEANT4 Simulation



Improvement (thinning? frame rate) for AR-test beamline

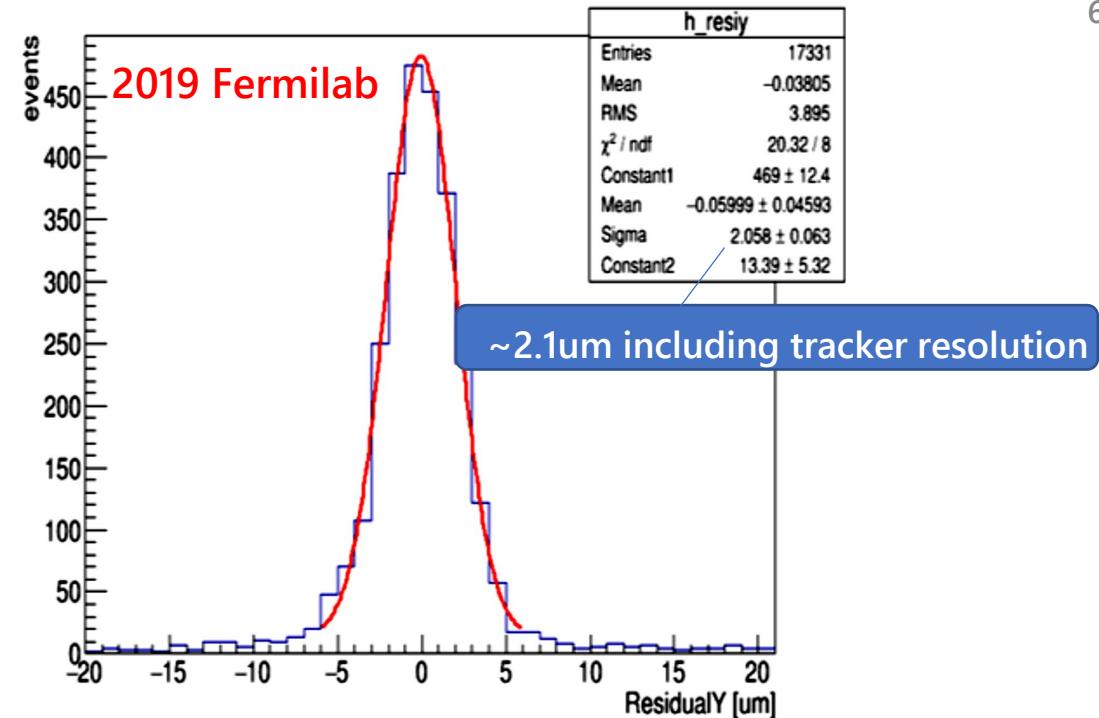
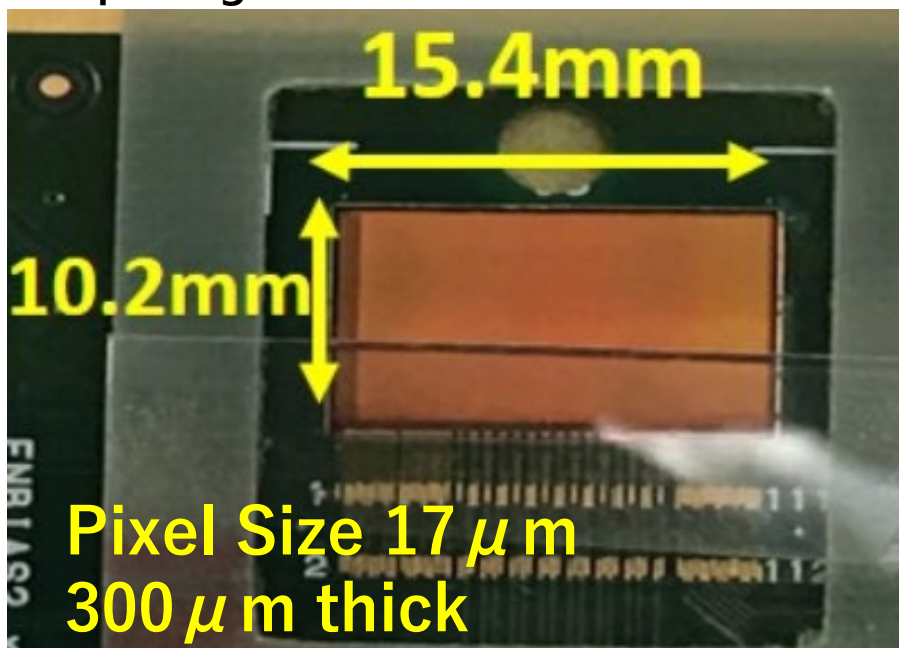


2022 Dutip Evaluation

# “INTPIX4NA” sensor

- ◆ Fine pixel size ( $17\mu\text{m} \times 17\mu\text{m}$ )
- ◆ Large sensitive area ( $14\text{mm} \times 9\text{mm}$ )
- ◆ Parallel 13-blocks analog outputs
- digitized off-chip with ADCs on dedicated DAQ board SEBAS2

Chip image

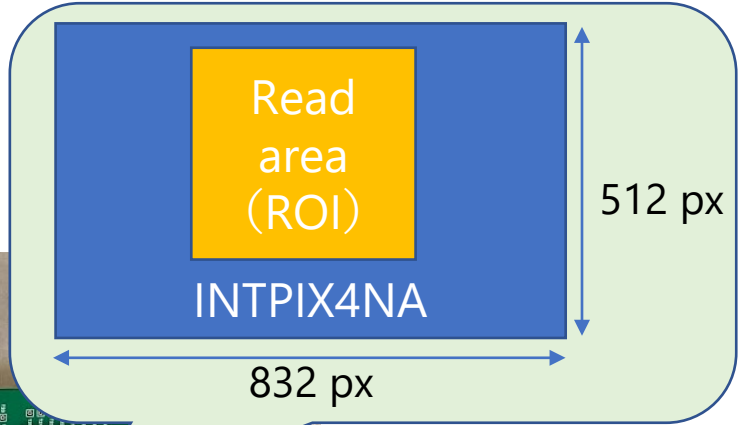
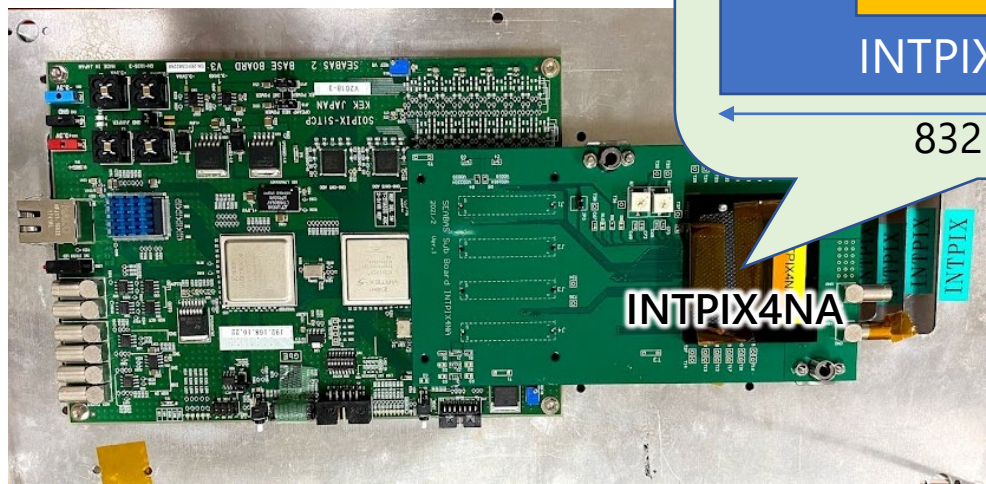


- ◆ 2019 INTPIX4 (500 $\mu\text{m}$  thick) @120GeV proton
- ◆ Intrinsic position resolution of  $\sim 1.5\mu\text{m}$

センサー	残差分布幅 [ $\mu\text{m}$ ]	Tracking Factor	位置分解能 [ $\mu\text{m}$ ]
INTPIX1	2.14±0.08	1.58	1.35±0.05
INTPIX2	1.75±0.04	1.29	1.34±0.03
INTPIX3	2.03±0.07	1.30	1.56±0.05
INTPIX4	2.55±0.14	1.55	1.65±0.09

INTPIX4 Position resolution (500 $\mu\text{m}$  thick)

# Readout system



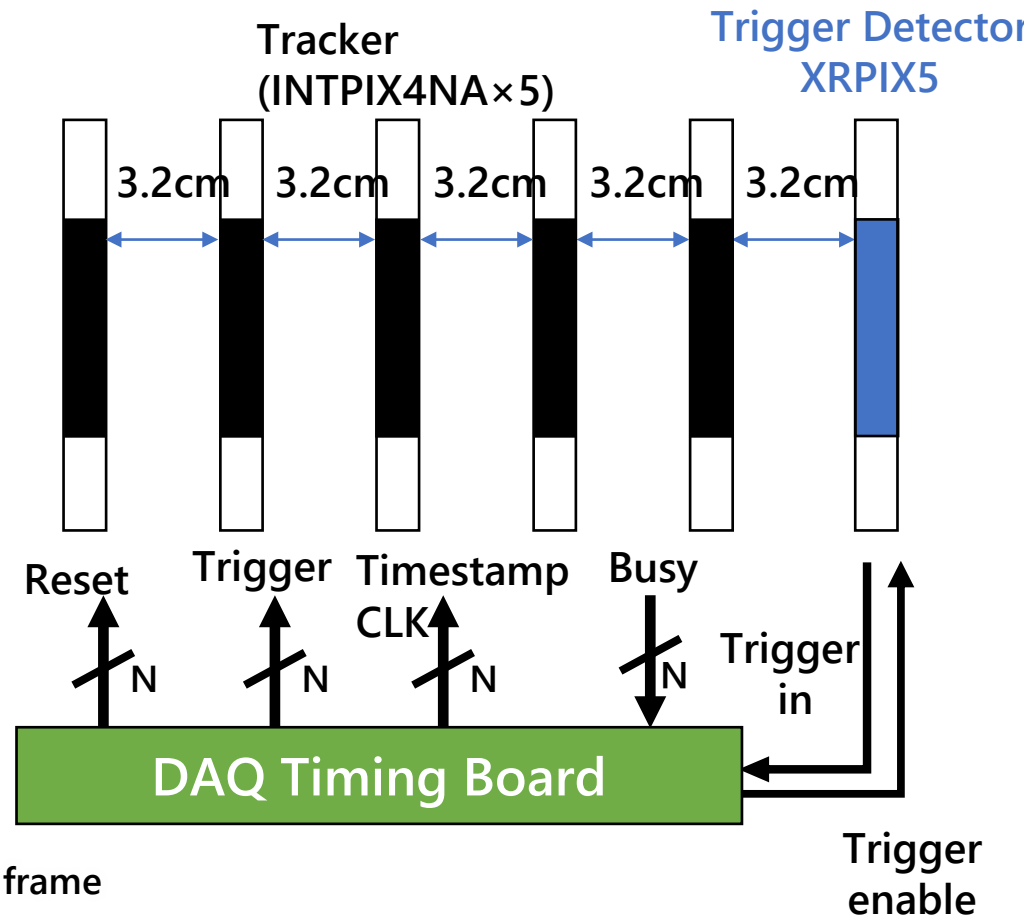
- ◆ SEBAS2(FPGA based) board + sub-board
- ◆ Region of Interest (ROI) can be set
- ◆ Chip repeats Integration & Reset until trigger is set
- ◆ Distribute control signals from the Timing board
  - ✓ Reset 5 INTPIX4NA sensors simultaneously
  - ✓ XRPIX issues Trigger on recording beam hit
  - ✓ Trigger starts readout in each sensor (BUSY is Set)
  - ✓ Guarantee synchronization by adding time information (time stamp) to each frame
  - ✓ Not accept triggers while BUSY is set in any of 5 sensors

## Trigger



Repeat Integration & Reset

Readout after Trigger signal

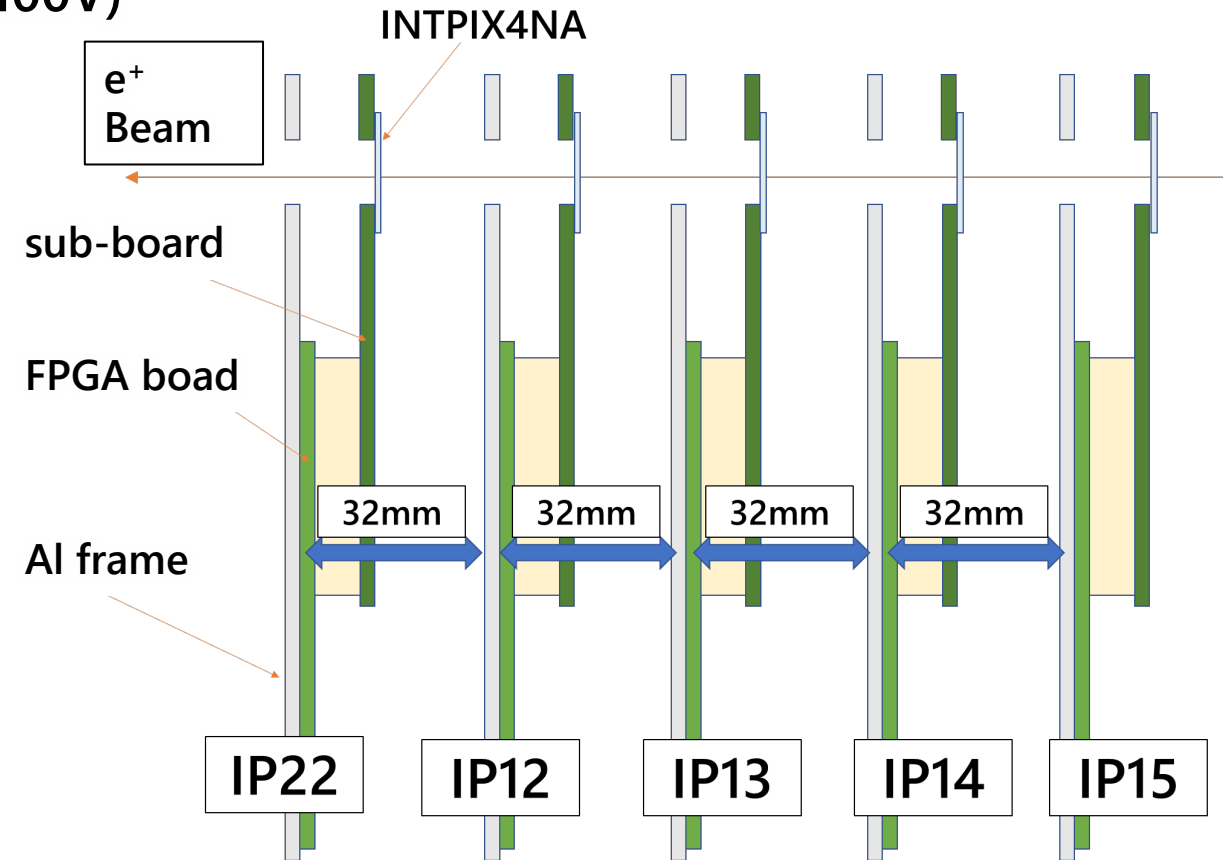
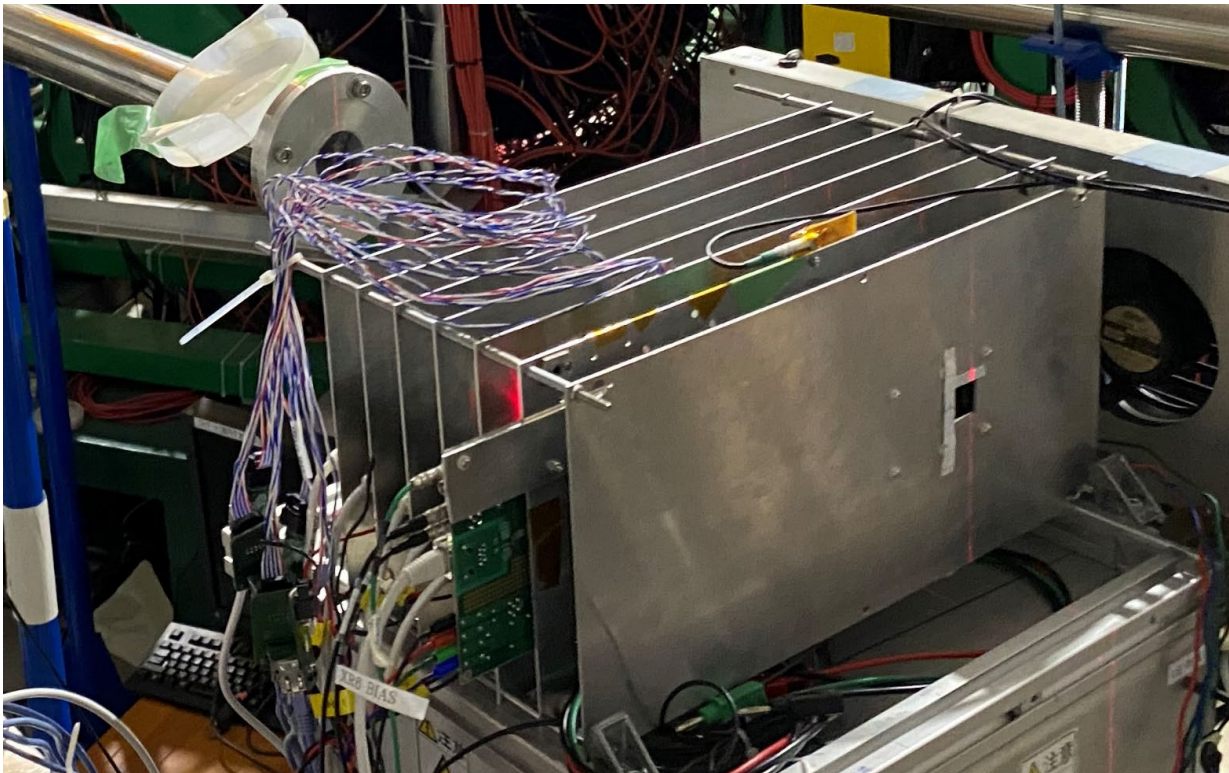


# 820MeV/c Electron Beam Performance Evaluation

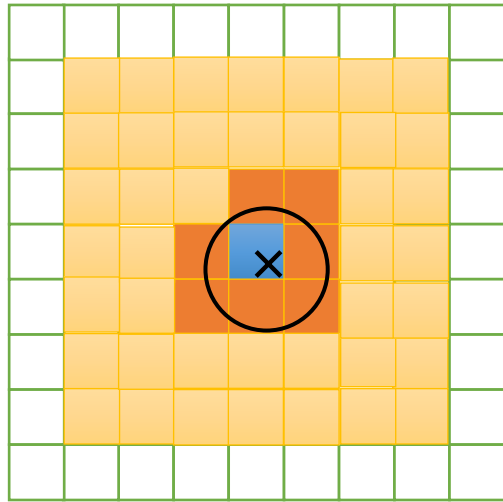


# ELPH 820MeV/c positron beam test

- Clustering • S/N evaluation
- Position resolution evaluation in various DUT-tracker plane configuration
  - ✓ Nominal beam momentum 820MeV/c (momentum scan 200-820MeV/c)
  - ✓ Nominal bias voltage 20V (HV scan 1V ~ 100V)

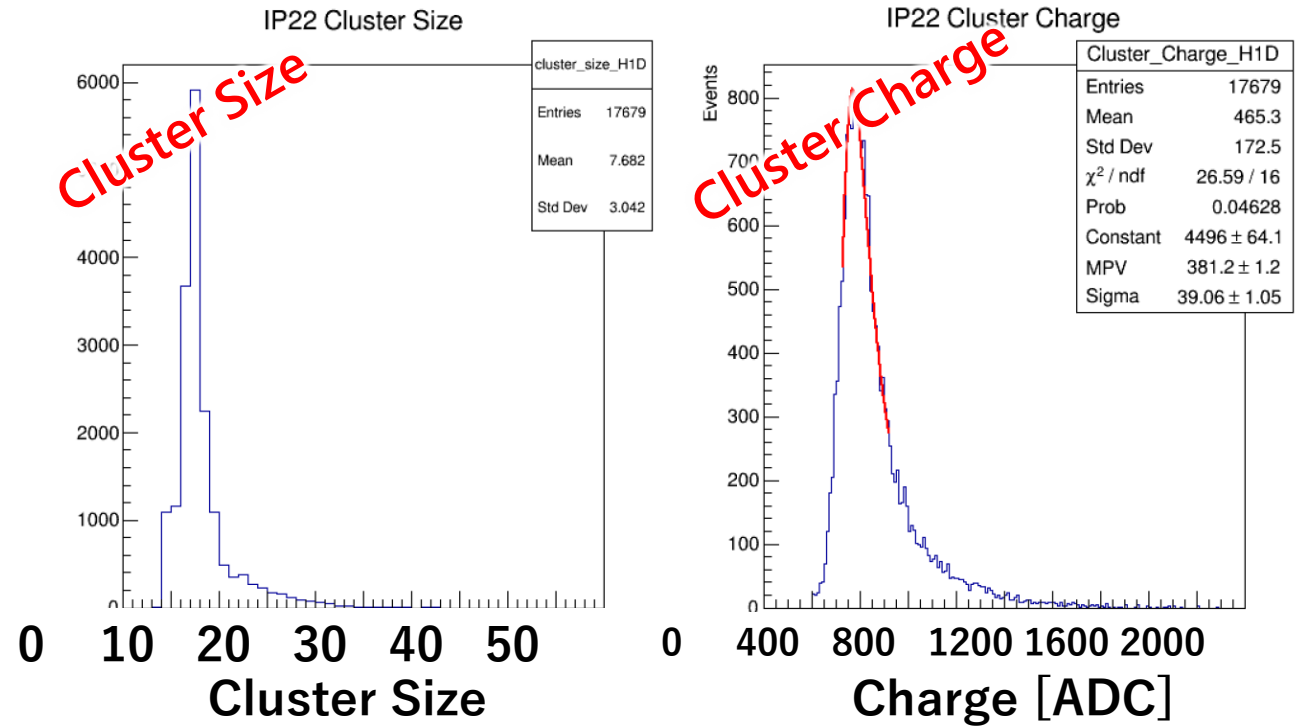


# Clustering • S/N evaluation



## clustering

- Cluster seed
- Cluster range
- Extracted pixels
- X Hit position  
Charge share



- Signal charge is shared by neighbor pixels
- the cluster spreads over 6-7 px in average
- ➔ Position resolution improved by a charge centroid method
- Evaluate the S/N ratio from the cluster charge

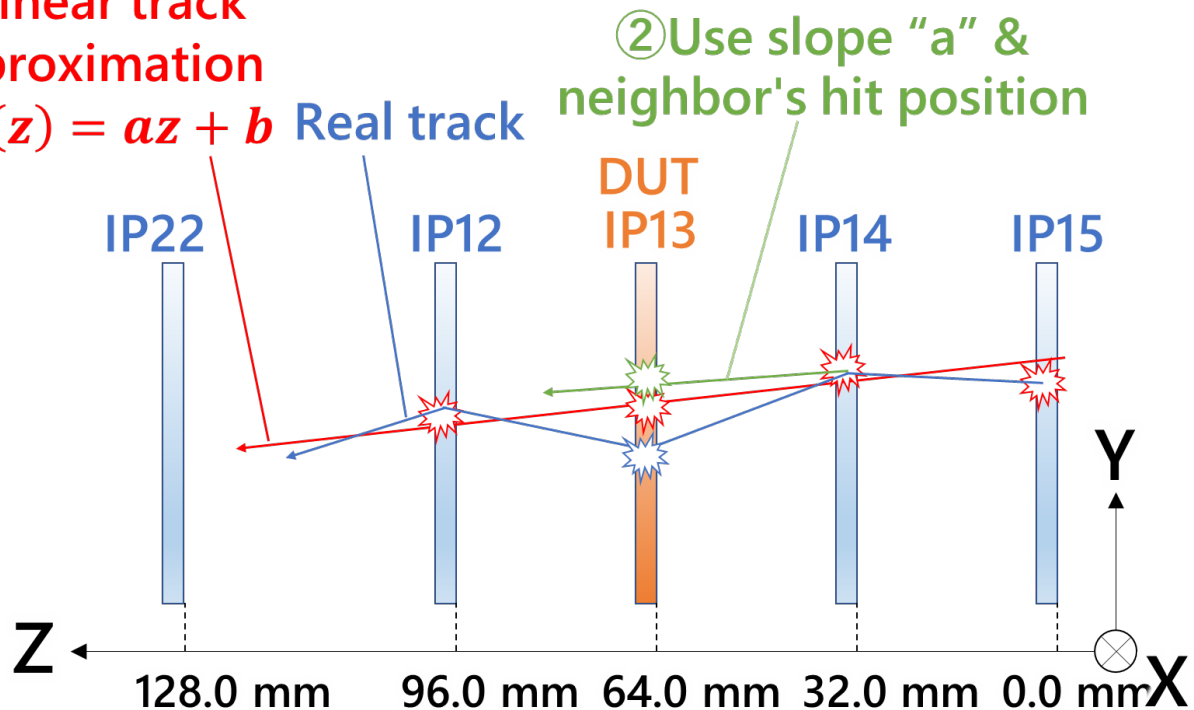
IP	noise	signal	S/N
IP22	1.6	381	237
IP12	1.8	339	188
IP13	1.8	354	188
IP14	1.7	275	156
IP15	1.6	382	242

# Track reconstruction

## 820 MeV/c positron beam

① linear track approximation

$$f(z) = az + b$$



② Use slope "a" & neighbor's hit position

Tracking Method

DUT → #3-2-1  
 Number of upstream side tracker (3)    Number of downstream side tracker (1)

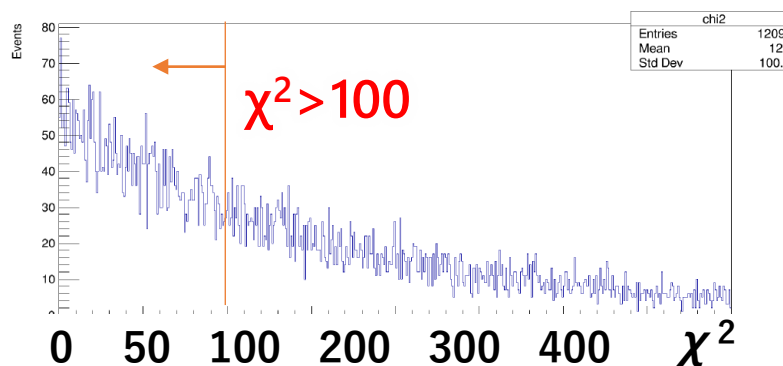
① Linear approximation

DUT	Tracking Method	$\sigma_x$ [um]
13	1-1	$12.15 \pm 0.10$
13	1-1	$14.48 \pm 0.12$
13	2-1	$14.42 \pm 0.12$
13	2-2	$20.28 \pm 0.16$

② Use slope "a" & neighbor's hit position

DUT	Tracking Method	$\sigma_x$ [um]
13	1-1	$12.15 \pm 0.10$
13	1-1	$12.18 \pm 0.10$
13	2-1	$11.80 \pm 0.10$
13	2-2	$14.57 \pm 0.12$

- Track reconstruction with INTPIX4NA itself as DUT
- Highly scattered tracks are degrading 2-2 track resolution

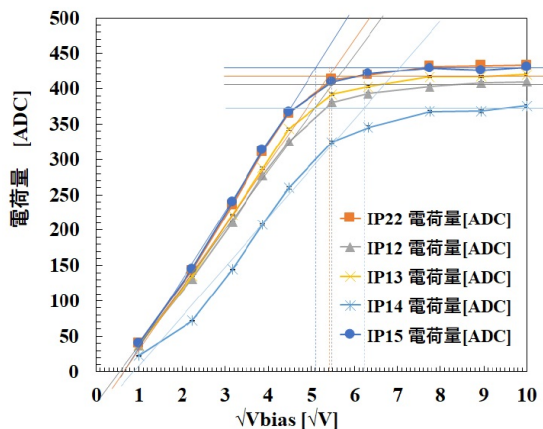


③  $\chi^2$  cut

DUT	Tracking Method	$\sigma_x$ [um]
13	1-1	$12.15 \pm 0.10$
13	1-1	$10.29 \pm 0.12$
13	2-1	$10.25 \pm 0.12$
13	2-2	$12.22 \pm 0.12$

# HV scan

- Apply 1-100V to all sensors
- Evaluate the full-depletion voltage



IP	Full-depletion voltage [V]
IP22	26.01
IP12	30.25
IP13	29.16
IP14	38.44
IP15	26.01

- Cluster size is maximum at 20V
  - ✓ Increase of the depletion thickness in  $V < 20V$ , spread suppressed by stronger electric field in  $V > 20V$
- Even if the cluster charge drops to 1/3, the resolution doesn't degrade.

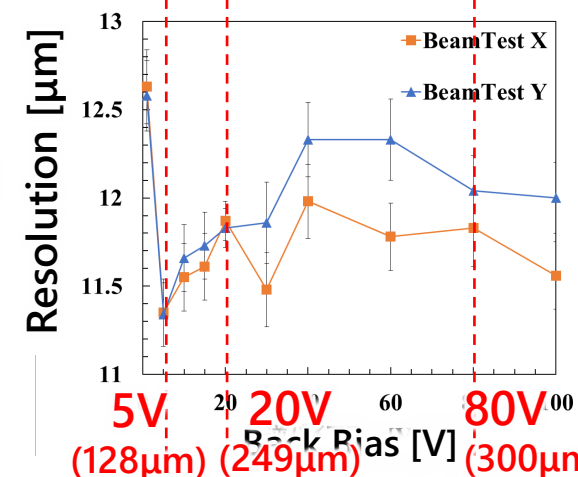
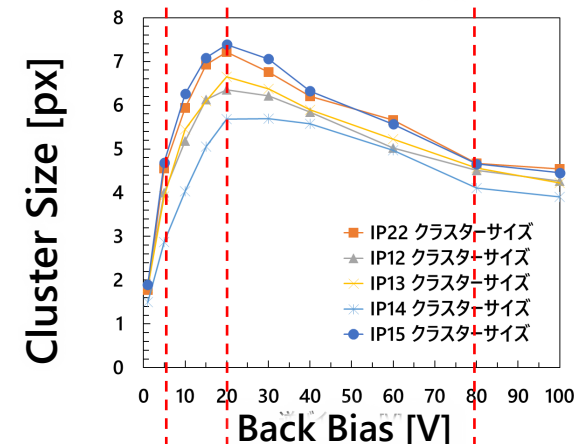
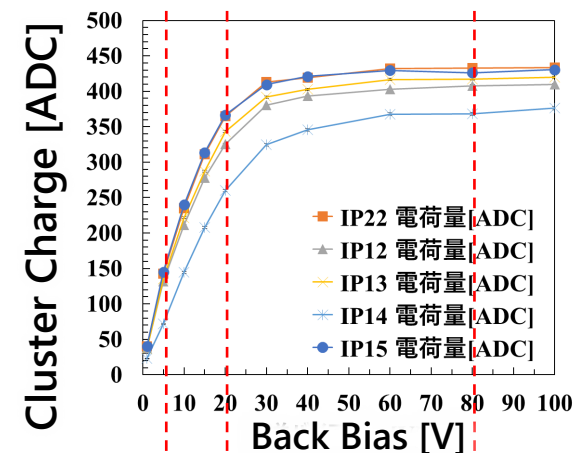
depletion thickness  $\sim 130\mu\text{m}@5V$ ,  $\sim 250\mu\text{m}@20V$

➔ low scattering & fine resolution are possible by thinning

Cluster Charge

Cluster Size

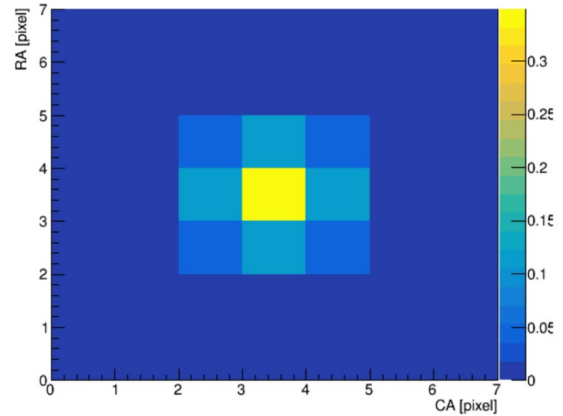
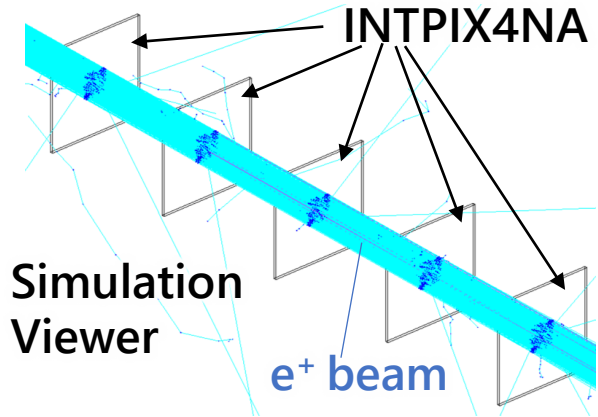
2-1 tracking resolution



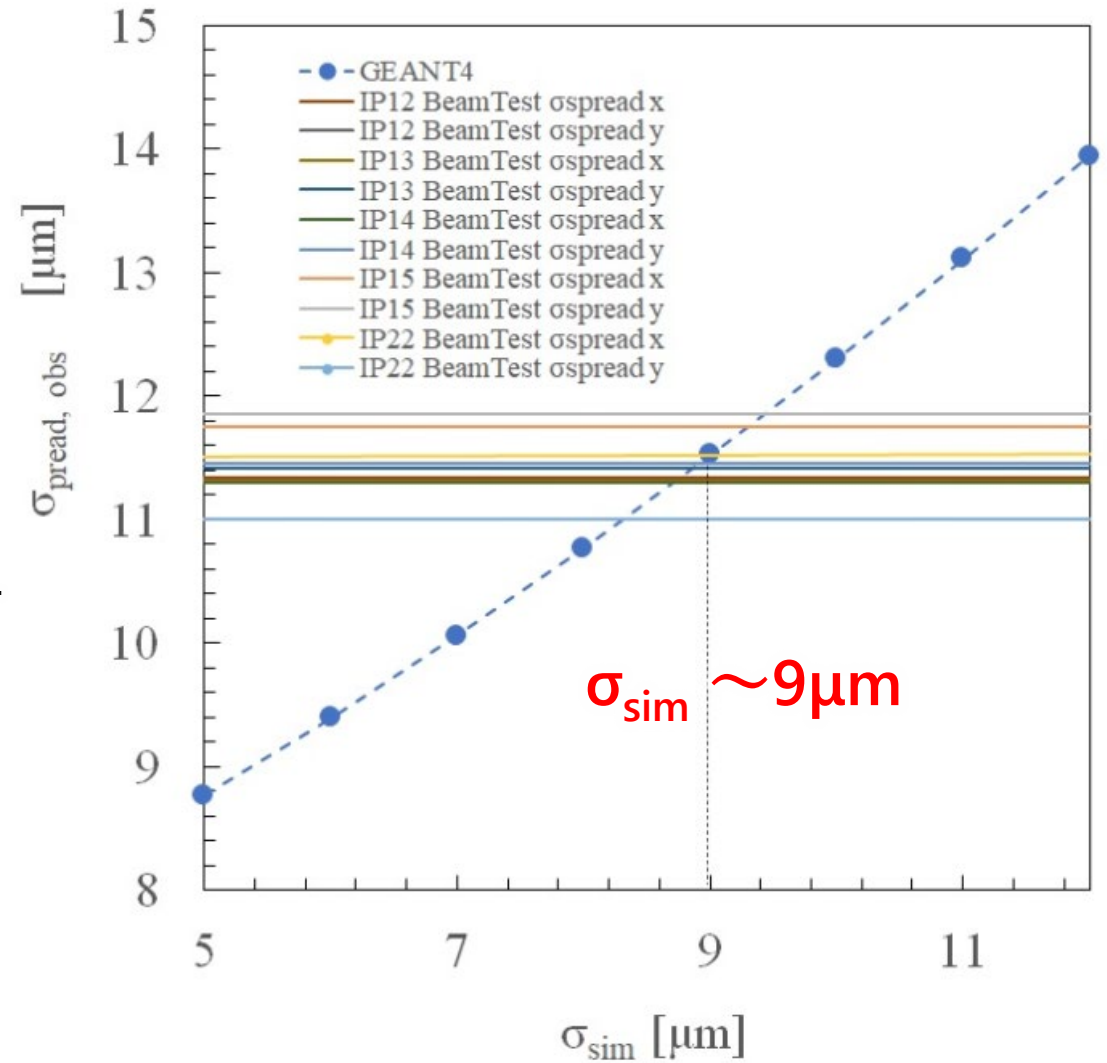
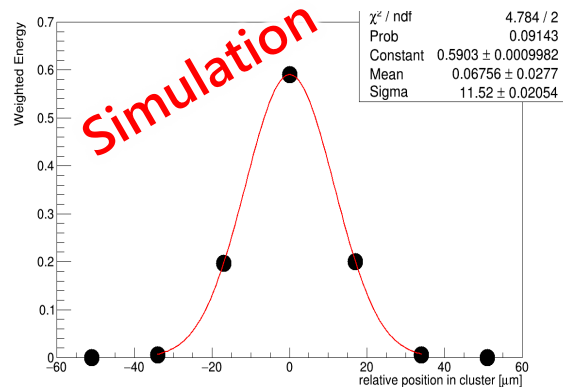
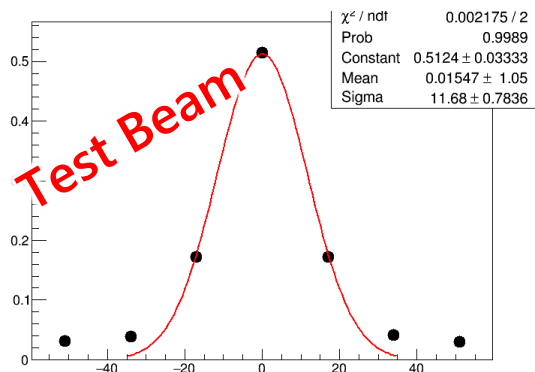
# GEANT4 Simulation

# Geant4 Simulation

- Charge spread is added about the charge deposition by a two-dimensional Gaussian with standard deviation  $\sigma_{sim}$



- spread among pixels is evaluated by fitting a Gauss to 1-D projections as  $\sigma_{spread}$
- ➔ set  $\sigma_{sim} = 9\mu m$  from comparison with beam test

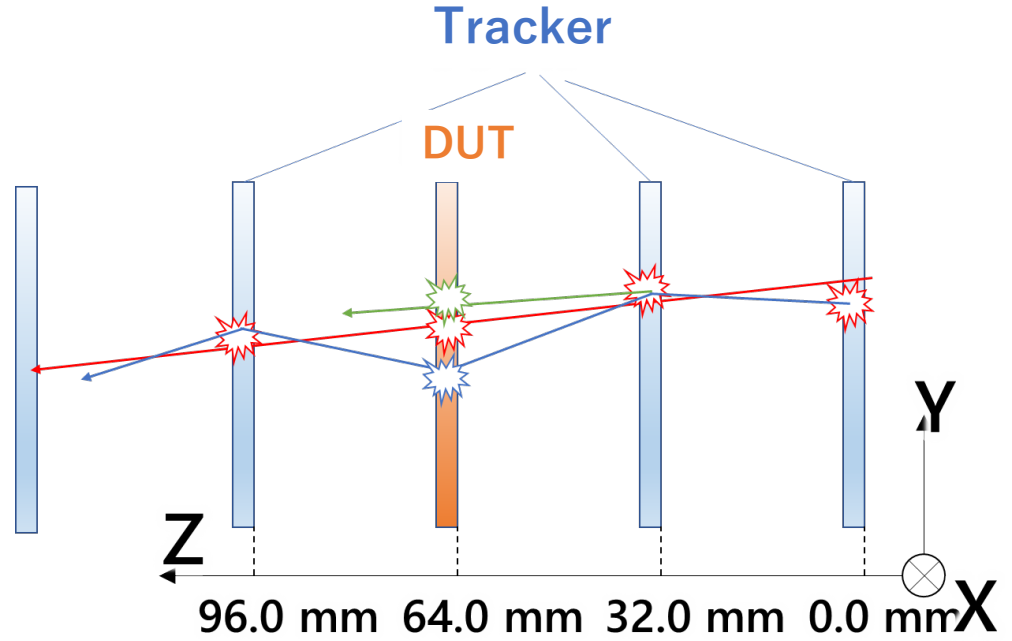
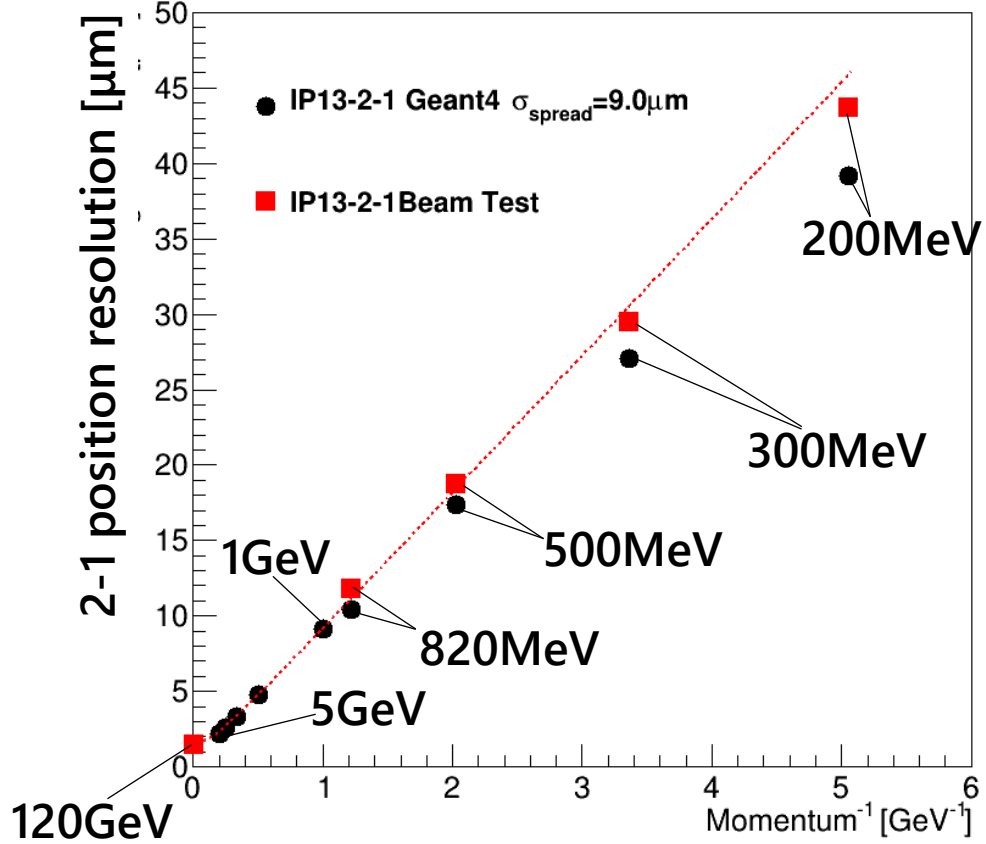


# Geant4 Simulation Resolution@1~5GeV

➤ Calculate the position by the charged centroid method

➔ Track reconstruction with 2-1

Simulate with 200 - 820MeV, 1 - 5GeV/c



➤ 2-1 resolution results of beam test (200 - 820MeV/c, 120GeV/c) are

$$\sigma_{obs} \sim \sqrt{\underbrace{\sigma_{trk}^2}_{\text{Tracking resolution}} + \underbrace{\frac{\sigma_{sct}^2}{P^2}}_{\text{Scattering effect}}}$$

➤ Estimate the resolution @5GeV/c

2.209 μm ± 0.02 μm  
Geant4

2.68 ± 0.14 μm  
prediction from  
beam-test fit

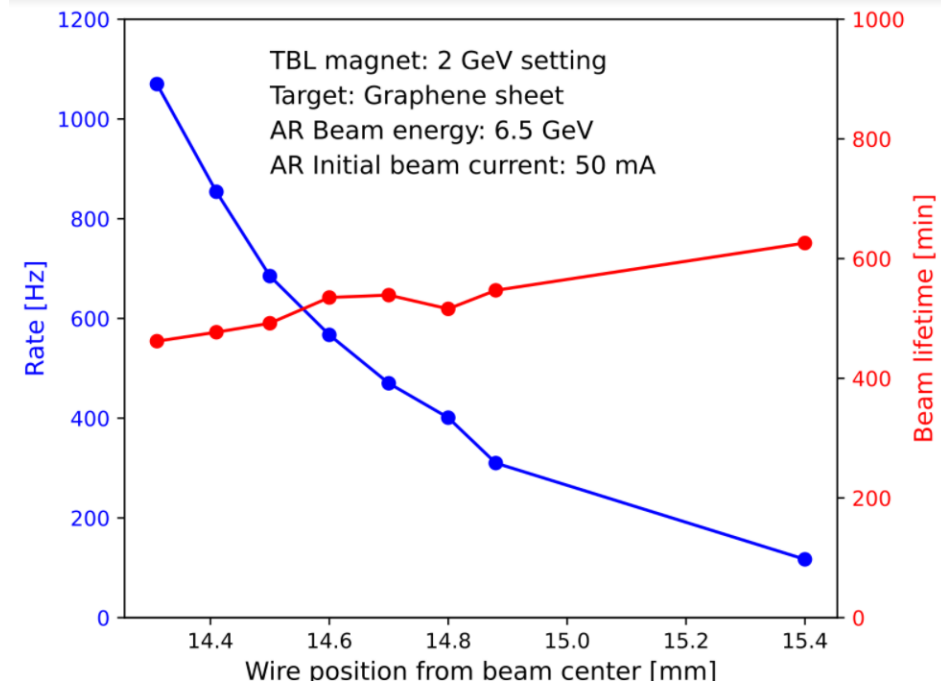
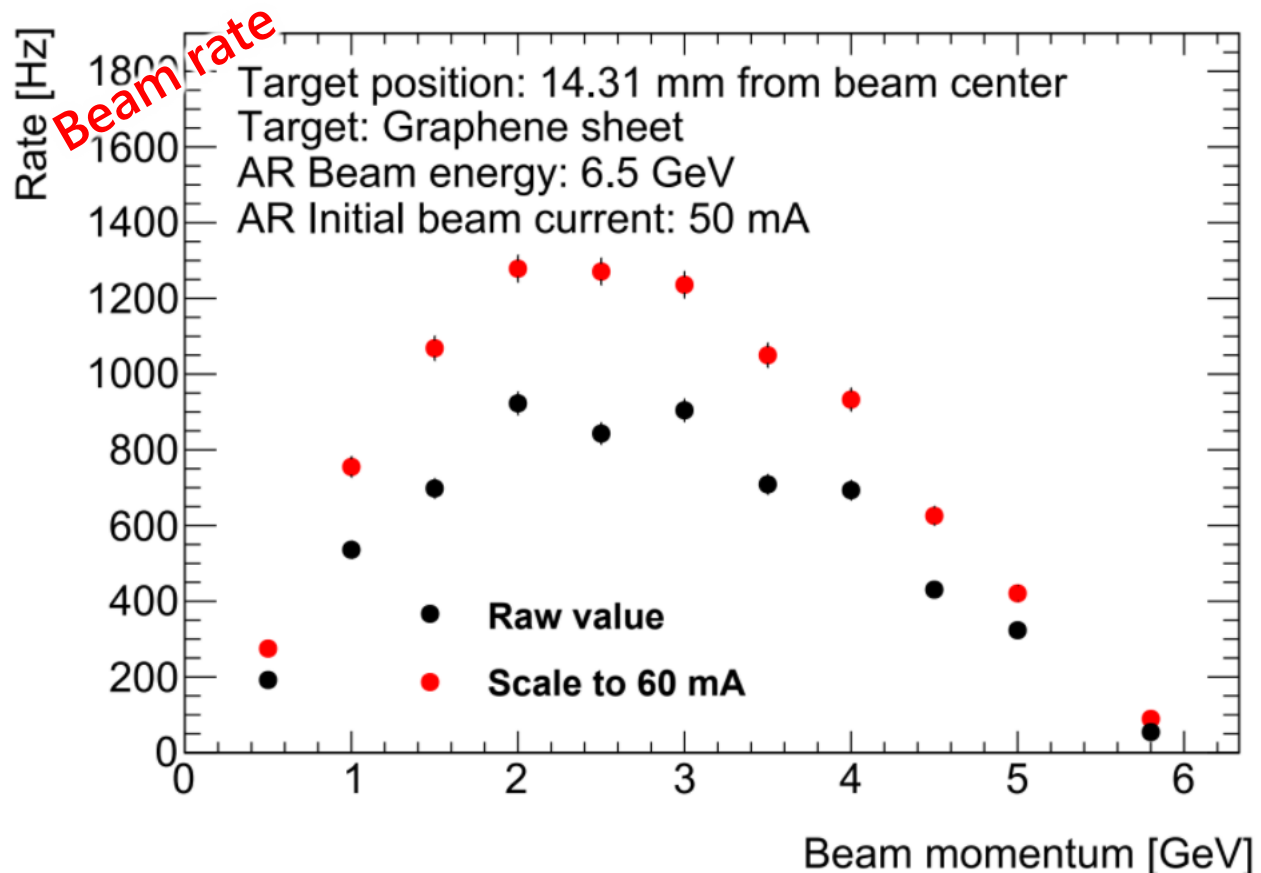
# Summary

- Constructed a high-precision, low-multiple-scattering telescope for KEK AR-TB using SOI pixel detectors
- Performance verification by beam test at ELPH
  - ✓ Position resolution evaluation (Momentum scan, HV scan)
  - ✓ resolution~12 $\mu\text{m}$  for 820 MeV/c positrons
- Performance prediction by Geant4 Simulation and ELPH/Fermilab data
  - ✓ Position resolution prediction 2.2~2.7 $\mu\text{m}$  @5GeV
  - ✓ We will improve the system for AR-TB

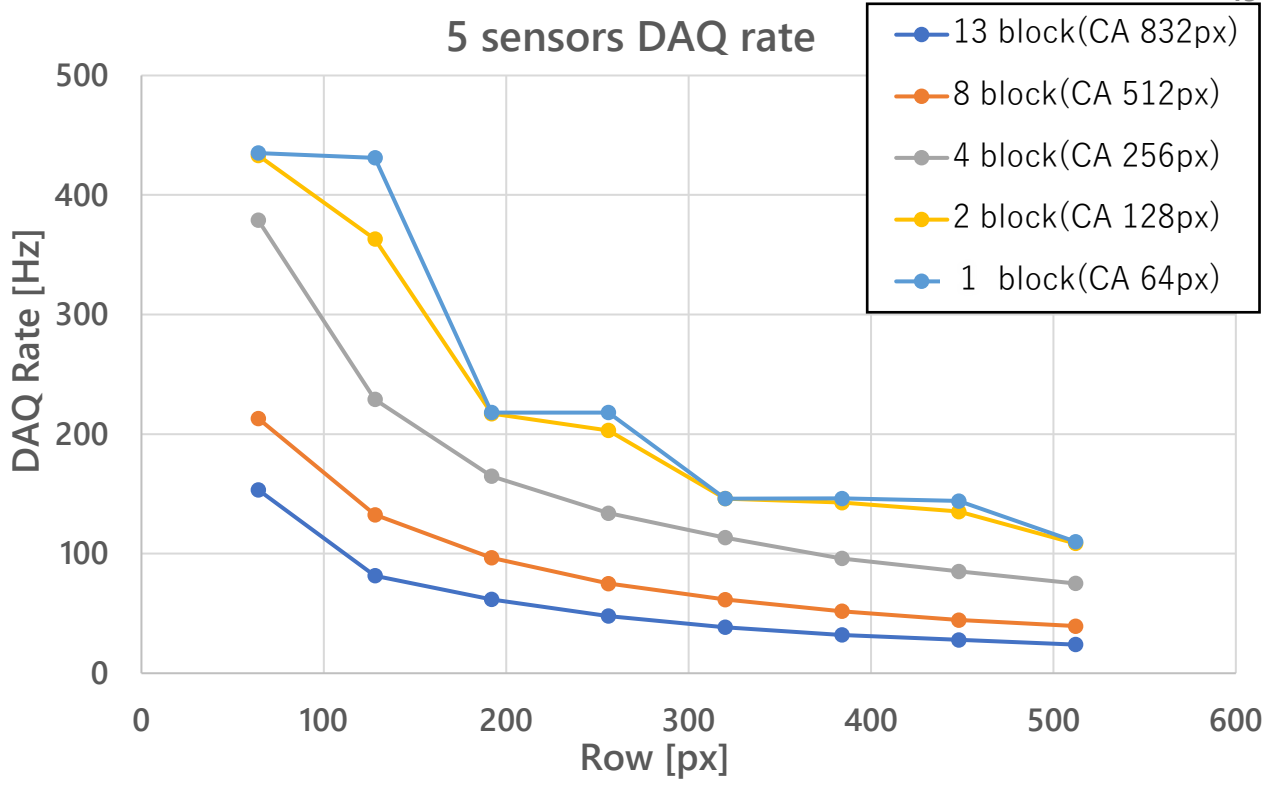
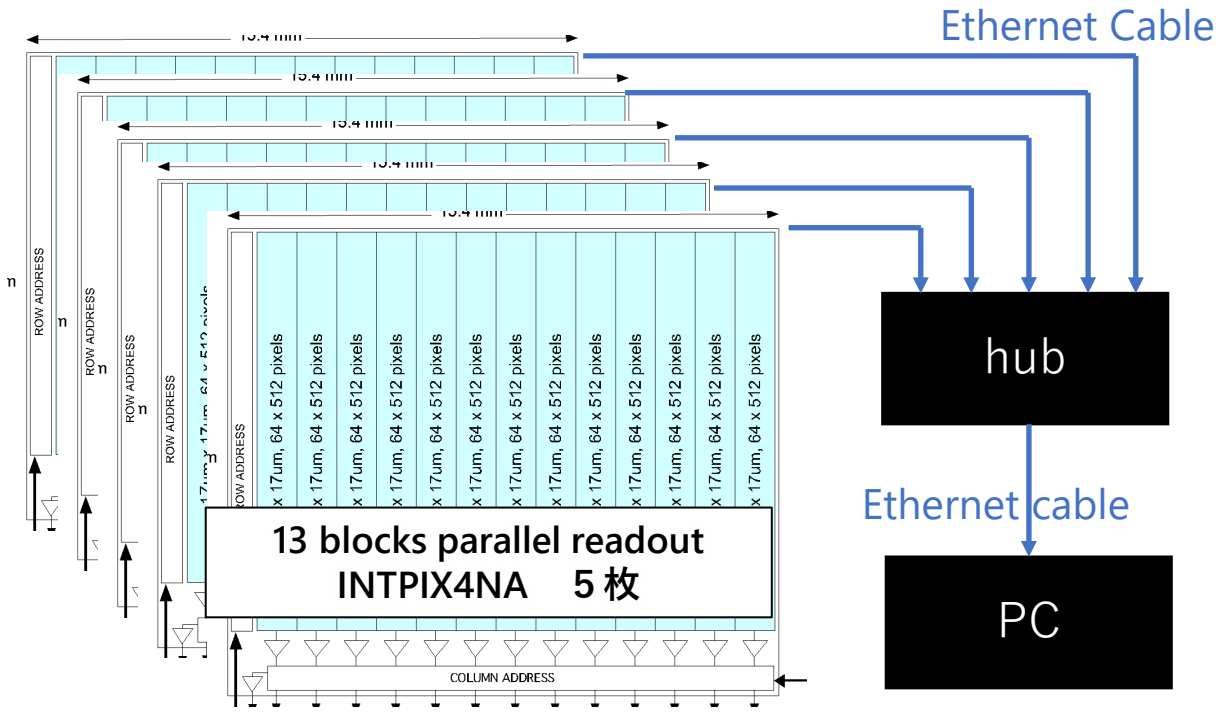


# Back up

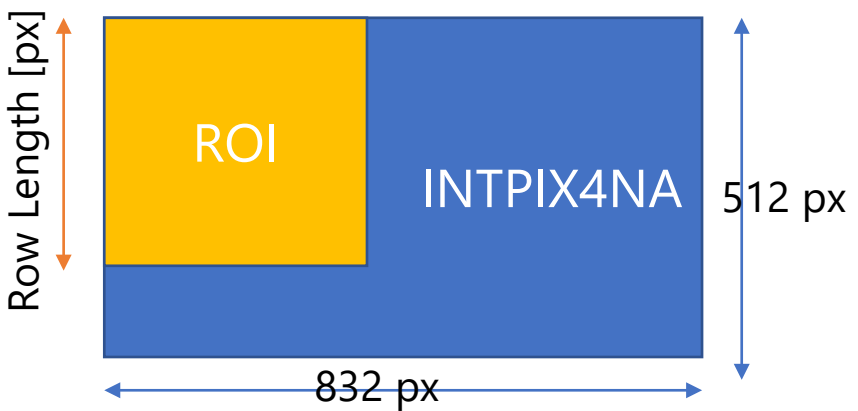
# AR-TB Beam information



# 5 sensors sync. —DAQ rate—

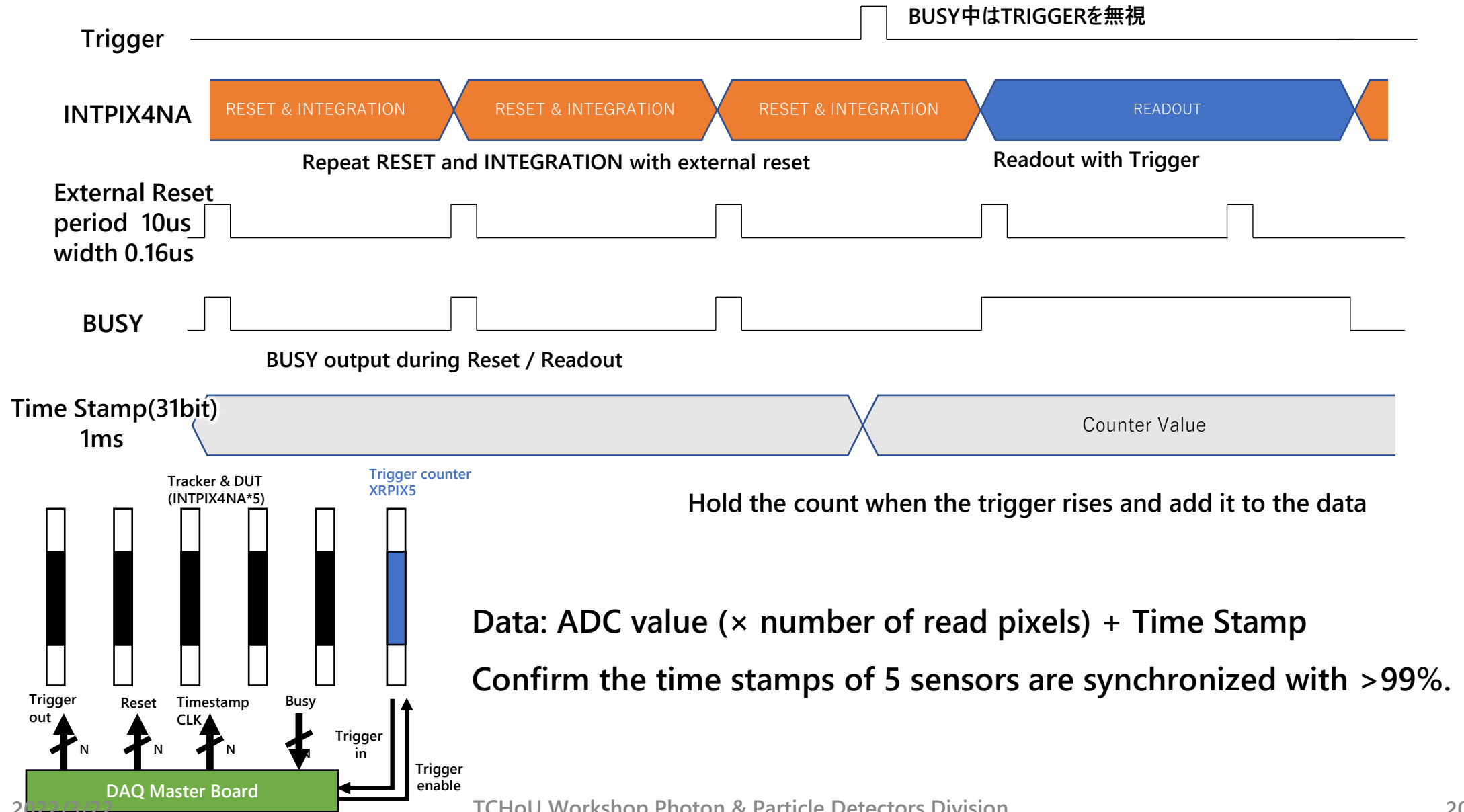


Column Length [px]



- ◆ Readout area can be selected by ROI
  - 512px \* 512px(40Hz) ~ 64px\*64px(400Hz)
- ◆ KEK AR-TB predicts 200-300Hz events for the chip size
  - Reduction of readout bits and development of zero suppression

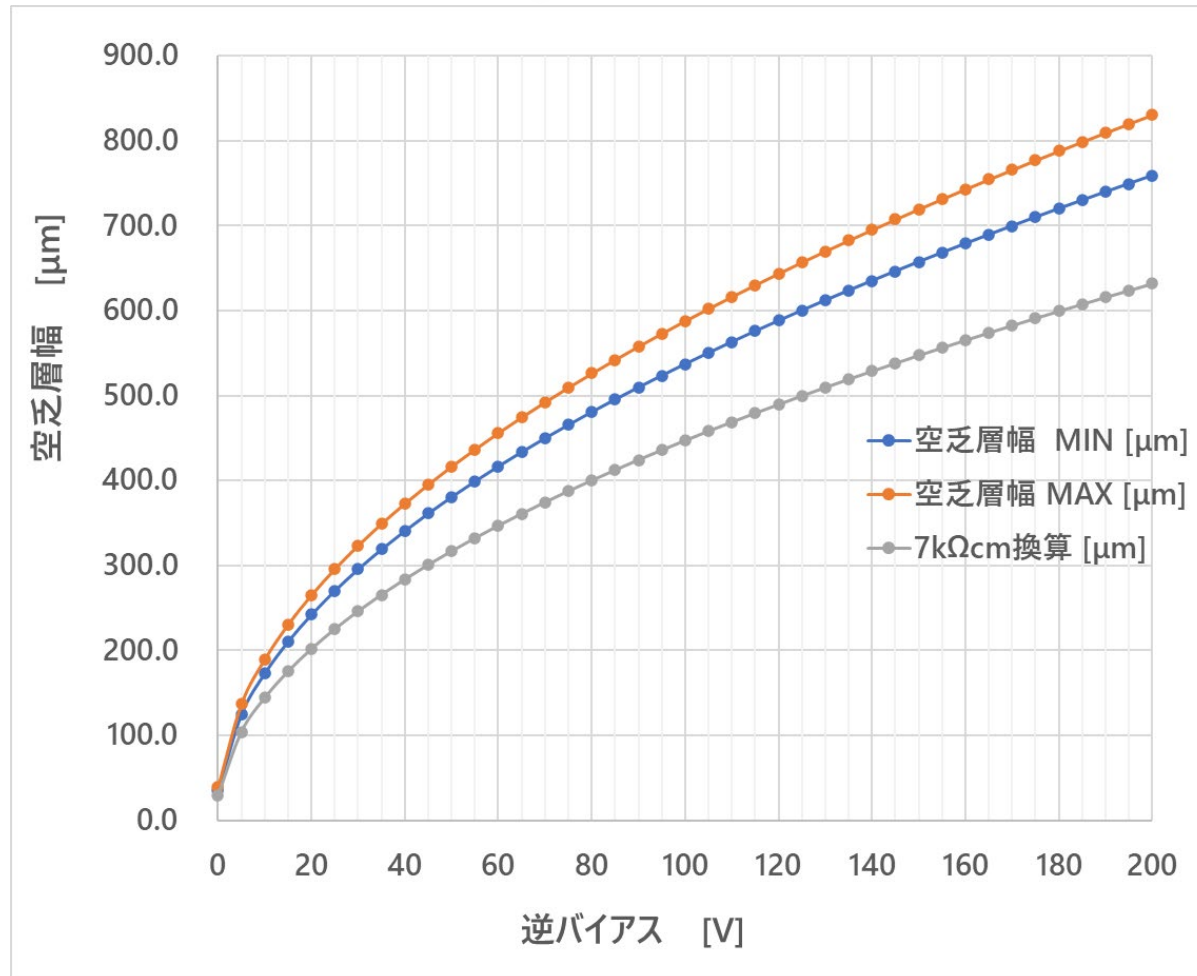
# 5 sensors sync. — time chart / synchronization —



# Depletion layer thickness of INTPIX4NA

- Depletion layer thickness of INTPIX4NA calculated for resistivity (10.1 ~ 12.1kΩcm)

(7kΩcm is the estimated resistivity value of INTPIX4 from 2019 beam test)



逆バイアス [V]	空乏層幅 MIN [μm]	空乏層幅 MAX [μm]	7kΩcm換算 [μm]
0	35.4	38.7	29.4
5	125.0	136.8	104.0
10	173.2	189.5	144.2
15	210.6	230.5	175.3
20	242.3	265.2	201.7
25	270.3	295.9	225.1
30	295.7	323.7	246.2
35	319.1	349.2	265.6
40	340.9	373.1	283.8
45	361.3	395.5	300.8
50	380.7	416.7	316.9
55	399.1	436.8	332.3
60	416.7	456.1	346.9
65	433.6	474.6	361.0
70	449.9	492.4	374.5
75	465.6	509.6	387.6
80	480.7	526.2	400.2
85	495.5	542.3	412.5
90	509.7	557.9	424.4
95	523.6	573.2	435.9
100	537.2	588.0	447.2
105	550.4	602.4	458.2
110	563.3	616.6	469.0
115	575.9	630.4	479.4
120	588.3	643.9	489.7
125	600.3	657.1	499.8
130	612.2	670.1	509.6
135	623.8	682.8	519.3
140	635.2	695.3	528.8
145	646.4	707.5	538.2
150	657.4	719.6	547.3
155	668.3	731.5	556.4
160	678.9	743.1	565.2
165	689.4	754.6	574.0
170	699.8	765.9	582.6
175	710.0	777.1	591.1
180	720.0	788.1	599.4
185	729.9	798.9	607.7
190	739.7	809.6	615.8
195	749.4	820.2	623.8
200	758.9	830.6	631.8

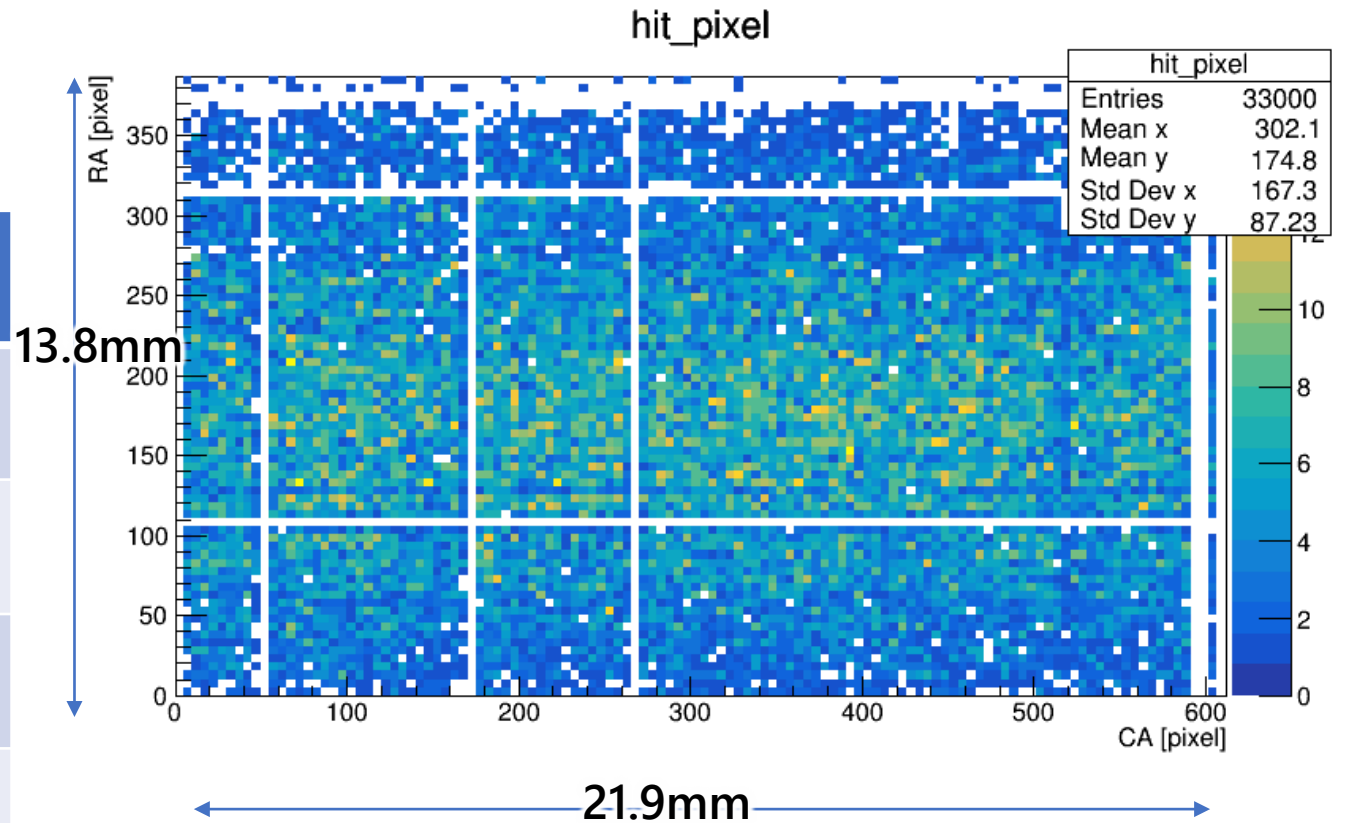
# ELPHビームテスト e<sup>+</sup>ビームセッティング、プロフィール

➤ Beam target: W (tungsten) 20 $\mu$ m

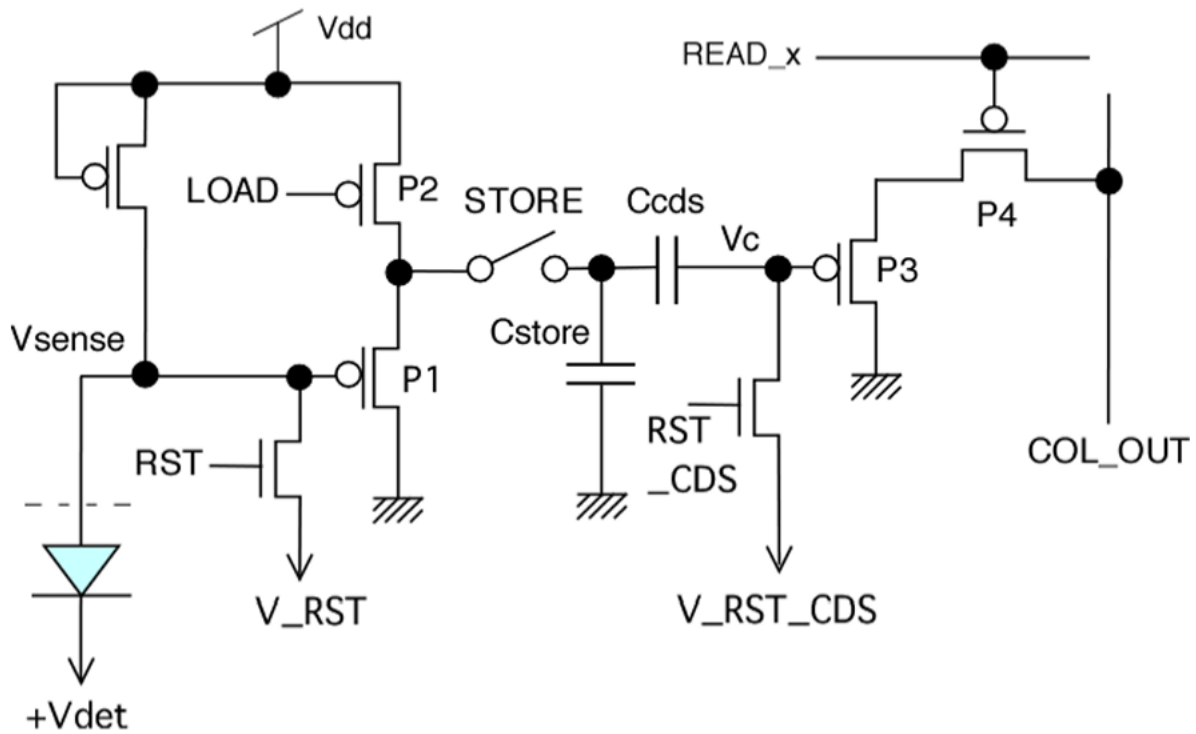
➤ Beam energy:

Current of electromagnet	momentum	Quadrupole magnet
100.0 A	197.79 MeV/c	QF=2T/m, QD=4T/m
150.0 A	297.30 MeV/c	QF=3T/m, QD=6T/m
250.0 A	492.5 MeV/c	QF=4T/m, QD=10T/m
475.0 A	822.37 MeV/c	QF=9T/m, QD=20T/m

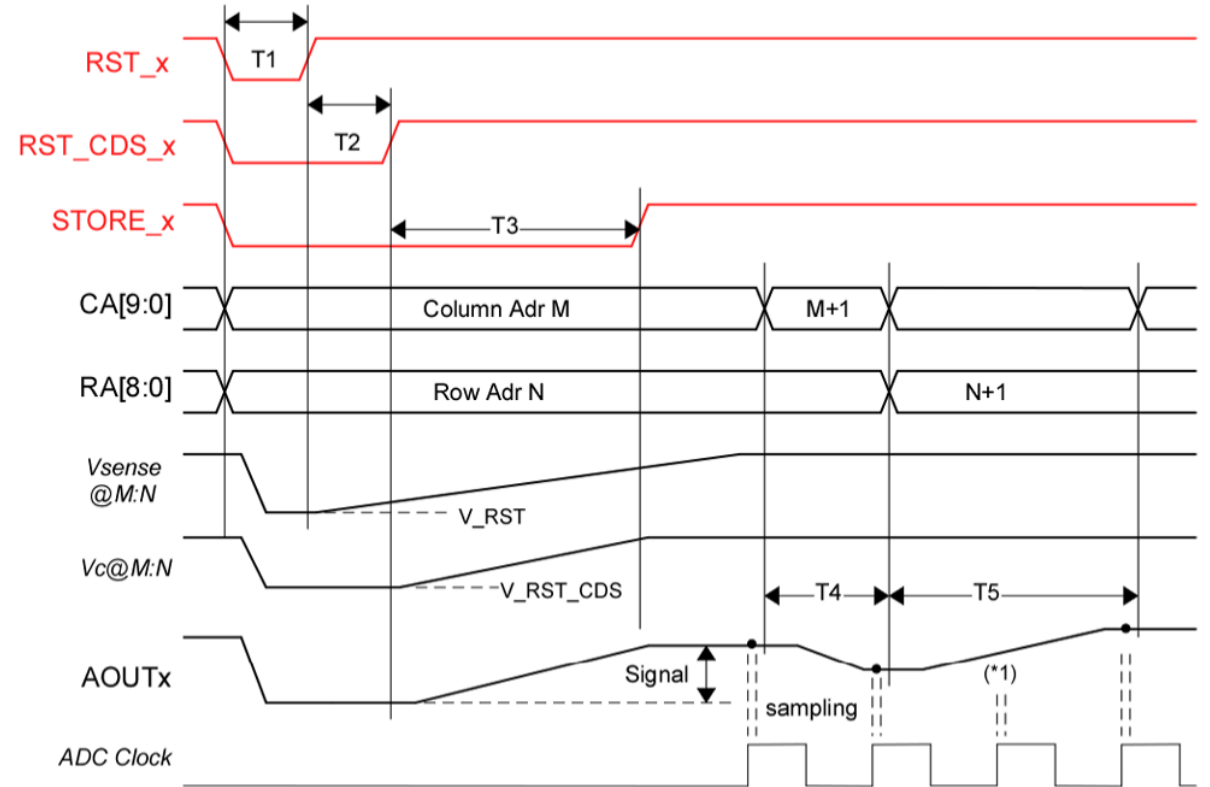
Beam profile confirmed with XRPIX5



# INTPIX4 circuit / logic



[AOUTx sampling timing]



(\*1)Skip the data in this cycle when the clock period is shorter than T5.